WHAT IS CLAIMED IS:

1. A processing method of a wafer, comprising:

a frame unit preparation step of fixing the wafer in an opening of an annular frame by an adhesion tape to prepare a frame unit;

a frame unit holding step of attracting and holding the wafer of the frame unit by a chuck table in an etching chamber with intermediary of the adhesion tape;

a shielding step of covering the annular frame and~~/or~~ an annular region of the adhesion tape exposed between the annular frame and the wafer by a cover member to shield the annular frame and the annular region from an external space;

wherein a bottom surface of an inner circumferential wall part of the cover member abuts against the adhesion tape to form a sealed space;

wherein the annular frame and the annular region of the adhesion tape are housed inside the sealed space; and

a dry etching step of supplying a gas to the etching chamber and executing dry etching for the wafer after execution of the frame unit holding step and the shielding step.

2. The processing method of a wafer according to claim 1, wherein

the annular frame is formed of a resin and the

annular frame is covered by the cover member in the shielding step.

3. The processing method of a wafer according to claim 1, wherein

plasma etching in which a gas in a plasma state is supplied is executed for the wafer in the dry etching step.

4. The processing method of a wafer according to claim 2, wherein

plasma etching in which a gas in a plasma state is supplied is executed for the wafer in the dry etching step.